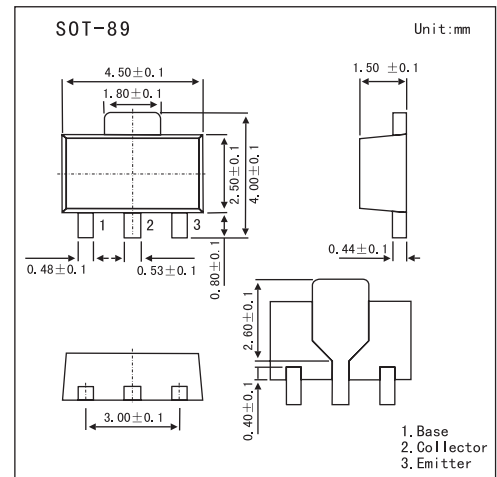


## Medium Power Transistor

### 2SD2391

#### ■ Features

- Low saturation voltage.
- Collector-emitter voltage =60V.
- PC=2 W (on 40×40×0.7mm ceramic board).



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	60	V
Collector-emitter voltage	V <sub>CEO</sub>	60	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current	I <sub>C</sub>	2	A
Collector power dissipation	P <sub>C</sub>	0.5	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV <sub>CB0</sub>	I <sub>C</sub> =50μA	60			V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA	60			V
Emitter-base breakdown voltage	BV <sub>EB0</sub>	I <sub>E</sub> =50μA	6			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =50V			0.1	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> =5V			0.1	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =50mA		0.13	0.35	V
DC current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A	120		270	
Output capacitance	f <sub>T</sub>	V <sub>CE</sub> =2V, I <sub>E</sub> =-0.5A, f=100MHz		210		MHz
Transition frequency	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz		21		pF

#### ■ Marking

Marking	DTQ
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